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Light Trapping in High Efficiency Interdigitated Back Contact Si Solar Cells



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Basic solar cell overview

- Solar spectrum
- Different types of solar cells
- Advantages of c-Si cell

Light Trapping in Thin Film Solar Cells

- Absorption loss and need of light trapping
- Make nano-patterns over large area
- Prior work in thin silicon films
- IBC cell for >20% efficiency
 - Combining Electron and Photon Harvesting

Conclusion

Solar basics

Solar Radiation Spectrum



Different types of solar cells





GaAs

$Cu(In,Ga)Se_2 \sim 1-2 \text{ um}$

c-Si ~ 180 um

http://web.stanford.edu/group/mcgehee/presentations/McGehee2011.pdf

Advantages of c-Si cell

Why c-Silicon solar cell?

- Natural abundance
- Non toxic
- Superior electronic properties
- Chemical/radiation hardness
- Low degradation over time
- Great heat resistant







Near band absorption loss

The absorption depth is the inverse of the absorption coefficient.



For the c-Si case where silicon strongly absorbs blue-green portion of the spectrum, the light trapping scheme is designed to trap light close to silicon band-edge where silicon is a weak absorber.

http://pveducation.org/pvcdrom/design/light-trapping



Need for light trapping



http://pveducation.org/pvcdrom/design/light-trapping

Electromagnetic Design Optimization

Light Trapping Geometry for 6 µm thick c-Si Wafer



(left) Schematic of trapped light inside thin-film silicon wafer as waveguide and cavity modes. The layout of diffractive optics schematic and SEM image of patterned Si surface.



FDTD predicted integrated absorption of AM1.5G spectrum in 6 μ m thick top diffractive optics etched c-Si wafer as a function of grating period (P) and relief depth (RD) for three duty (D/P) cycles of 0.25, 0.5 and 0.75 where D is the diameter of nanopillers.

Absorption of Solar Spectrum

•2D Si Grating Period = 500 nm, W =368 nm, H = 130 nm
•Si Slab = 5.87 μm + H (Total Length Simulation) = 6μm



Soft Lithography

PDMS Mold Making Soft Nanoimprinting PDMS mold Master made using DLW photoresist on substrate fabricate master patterned cast elastomer photoresist etch cure substrate Patterned peel back Substrate **PDMS** mold

Measurements data in 6 µm thick working light

trapping c-Si cells

Microbar c-Silicon Solar Cells

Soft Lithography based Hexagonal Light Trapping Pattern



Period = 500 nm, Relief Depth = 120 nm, Diameter = 375 nm



Light Trapping Efficiency = 9.5%

D. Chanda et. at., Nano Letters, 10, 3041-3046 (2010).

Light Trapping in 2.8 µm thick working c-Si cells



-Overall, efficiency improved by 237% -Max Efficiency = 10.8%

D. Chanda et. at., , Light Trapping in Ultra-thin Mono-crystalline Silicon Solar Cells", (Cover Article) Advanced Energy Materials , (DOI: 10.1002/aenm.201300542), Nov 2013.

Achieve high efficiency in thin c-Si solar cells

Light Trapping Pattern, Surface Passivation and Anti-Reflection Coating

Si nanopillars



APCVD Coated Si nanopillars



On going

IBC cell for > 20% Efficiency

Need combined Electron and Photon Harvesting

Minimizing carrier loss

- Passivation of front and back electrode
- Shallow doped p-n junction
- Locally p+ doped back surface field
- Minimizing photon loss
- Front textured surface.
- Single or multi layer ARC.
- Back contact cell structure
- Minimizing electrical loss
- Fine gridline front contact.
- Selective emitter n- or p-type Si substrate with minority carrier diffusion length longer than the base thickness.



25 µm interdigitated back contact (IBC) cell



-Graded Doping Profile for better Charge Separation -Interdigitated Contacts for better Charge Collection

Achieve 20% efficiency in 25 µm thick c-Si Wafer

The proposed hexagonal nanopillar array based light trapping scheme in presence of back side reflector demonstrated absorption of 78% of integrated solar spectrum in 3 μ m thick c-Si slab which scales up to 90% when implemented on 25 μ m thick wafer.



Fabricating 100 micron IBC cell





Image of hexagonal light trapping nanopillars on Silicon substrate Image of interdigitated contact of 1 cmxcm IBC solar cell Conclusions

 Absorption optimization of thin silicon solar cells with/out light trapping, ARC, BSR is studied and simulated.

- Thin silicon solar cells was fabricated and electronically characterized.
- Nano patterning was developed on large area, 6"×6".
- Ultimate goal is fabricating 25 µm c-Si solar cell with optimized light trapping and broadband coating design to absorb 100% of solar spectrum.

Thank you!

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